

PSMN026-80YS

N-channel LPAK 80 V 27.5 mΩ standard level MOSFET

Rev. 01 — 25 June 2009

Product data sheet

1. Product profile

1.1 General description

Standard level N-channel MOSFET in LPAK package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- Advanced TrenchMOS provides low $R_{DS(on)}$ and low gate charge
- High efficiency gains in switching power converters
- Improved mechanical and thermal characteristics
- LPAK provides maximum power density in a Power SO8 package

1.3 Applications

- DC-to-DC converters
- Lithium-ion battery protection
- Load switching
- Motor control
- Server power supplies

1.4 Quick reference data

Table 1. Quick reference

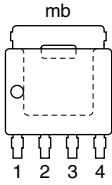
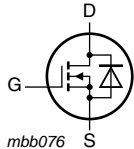
| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|--------------------------------|--|--|-----|-----|-----|------|
| V_{DS} | drain-source voltage | $T_j \geq 25\text{ °C}$; $T_j \leq 175\text{ °C}$ | - | - | 80 | V |
| I_D | drain current | $T_{mb} = 25\text{ °C}$; $V_{GS} = 10\text{ V}$; see Figure 1 | - | - | 34 | A |
| P_{tot} | total power dissipation | $T_{mb} = 25\text{ °C}$; see Figure 2 | - | - | 74 | W |
| T_j | junction temperature | | -55 | - | 175 | °C |
| Avalanche ruggedness | | | | | | |
| $E_{DS(AL)S}$ | non-repetitive drain-source avalanche energy | $V_{GS} = 10\text{ V}$; $T_{j(init)} = 25\text{ °C}$; $I_D = 31\text{ A}$; $V_{sup} \leq 80\text{ V}$; $R_{GS} = 50\text{ }\Omega$; unclamped | - | - | 32 | mJ |
| Dynamic characteristics | | | | | | |
| Q_{GD} | gate-drain charge | $V_{GS} = 10\text{ V}$; $I_D = 25\text{ A}$; | - | 5 | - | nC |
| $Q_{G(tot)}$ | total gate charge | $V_{DS} = 40\text{ V}$; see Figure 14 ; see Figure 15 | - | 20 | - | nC |

Table 1. Quick reference ...continued

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|-------------------------------|----------------------------------|--|-----|-----|------|------|
| Static characteristics | | | | | | |
| $R_{DS(on)}$ | drain-source on-state resistance | $V_{GS} = 10\text{ V}; I_D = 5\text{ A}; T_j = 100\text{ }^\circ\text{C};$ see Figure 12 | - | - | 42 | mΩ |
| | | $V_{GS} = 10\text{ V}; I_D = 5\text{ A}; T_j = 25\text{ }^\circ\text{C};$ see Figure 13 | - | 20 | 27.5 | mΩ |

2. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-----------------------------------|--|---|
| 1 | S | source |  <p>SOT669 (LPAK)</p> |  <p>mbb076</p> |
| 2 | S | source | | |
| 3 | S | source | | |
| 4 | G | gate | | |
| mb | D | mounting base; connected to drain | | |

3. Ordering information

Table 3. Ordering information

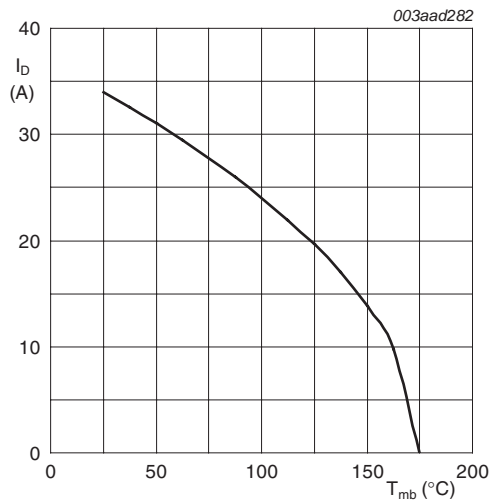
| Type number | Package | | Version |
|--------------|---------|--|---------|
| | Name | Description | |
| PSMN026-80YS | LPAK | plastic single-ended surface-mounted package (LPAK); 4 leads | SOT669 |

4. Limiting values

Table 4. Limiting values

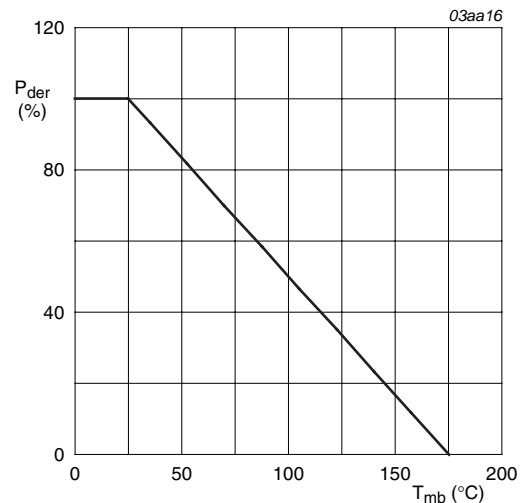
In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|-----------------------------|--|---|-----|-----|------|
| V _{DS} | drain-source voltage | T _j ≥ 25 °C; T _j ≤ 175 °C | - | 80 | V |
| V _{DGR} | drain-gate voltage | T _j ≥ 25 °C; T _j ≤ 175 °C; R _{GS} = 20 kΩ | - | 80 | V |
| V _{GS} | gate-source voltage | | -20 | 20 | V |
| I _D | drain current | V _{GS} = 10 V; T _{mb} = 100 °C; see Figure 1 | - | 24 | A |
| | | V _{GS} = 10 V; T _{mb} = 25 °C; see Figure 1 | - | 34 | A |
| I _{DM} | peak drain current | t _p ≤ 10 μs; pulsed; T _{mb} = 25 °C; see Figure 3 | - | 137 | A |
| P _{tot} | total power dissipation | T _{mb} = 25 °C; see Figure 2 | - | 74 | W |
| T _{stg} | storage temperature | | -55 | 175 | °C |
| T _j | junction temperature | | -55 | 175 | °C |
| T _{slid(M)} | peak soldering temperature | | - | 260 | °C |
| Source-drain diode | | | | | |
| I _S | source current | T _{mb} = 25 °C | - | 34 | A |
| I _{SM} | peak source current | t _p ≤ 10 μs; pulsed; T _{mb} = 25 °C | - | 137 | A |
| Avalanche ruggedness | | | | | |
| E _{DS(AL)S} | non-repetitive drain-source avalanche energy | V _{GS} = 10 V; T _{j(init)} = 25 °C; I _D = 31 A; V _{sup} ≤ 80 V; R _{GS} = 50 Ω; unclamped | - | 32 | mJ |



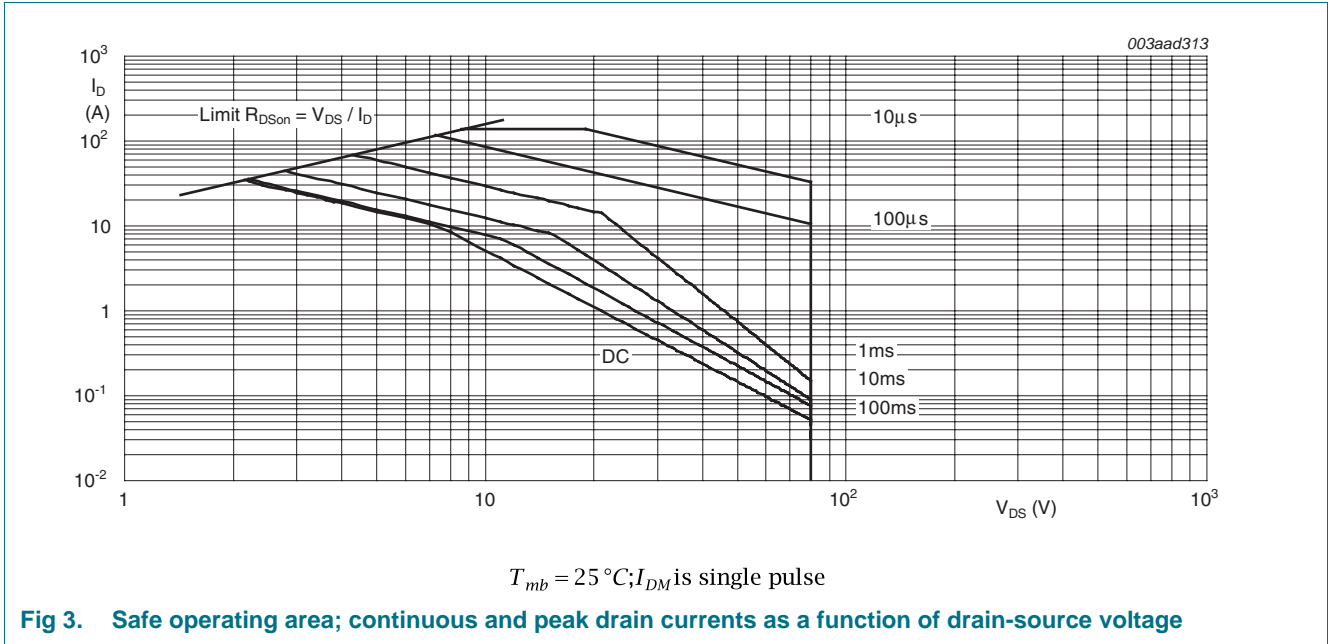
$$V_{GS} \geq 10\text{ V}$$

Fig 1. Continuous drain current as a function of mounting base temperature



$$P_{der} = \frac{P_{tot}}{P_{tot(25^\circ\text{C})}} \times 100\%$$

Fig 2. Normalized total power dissipation as a function of mounting base temperature



5. Thermal characteristics

Table 5. Thermal characteristics

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|----------------|---|------------------------------|-----|-----|-----|------|
| $R_{th(j-mb)}$ | thermal resistance from junction to mounting base | see Figure 4 | - | 1.4 | 2 | K/W |

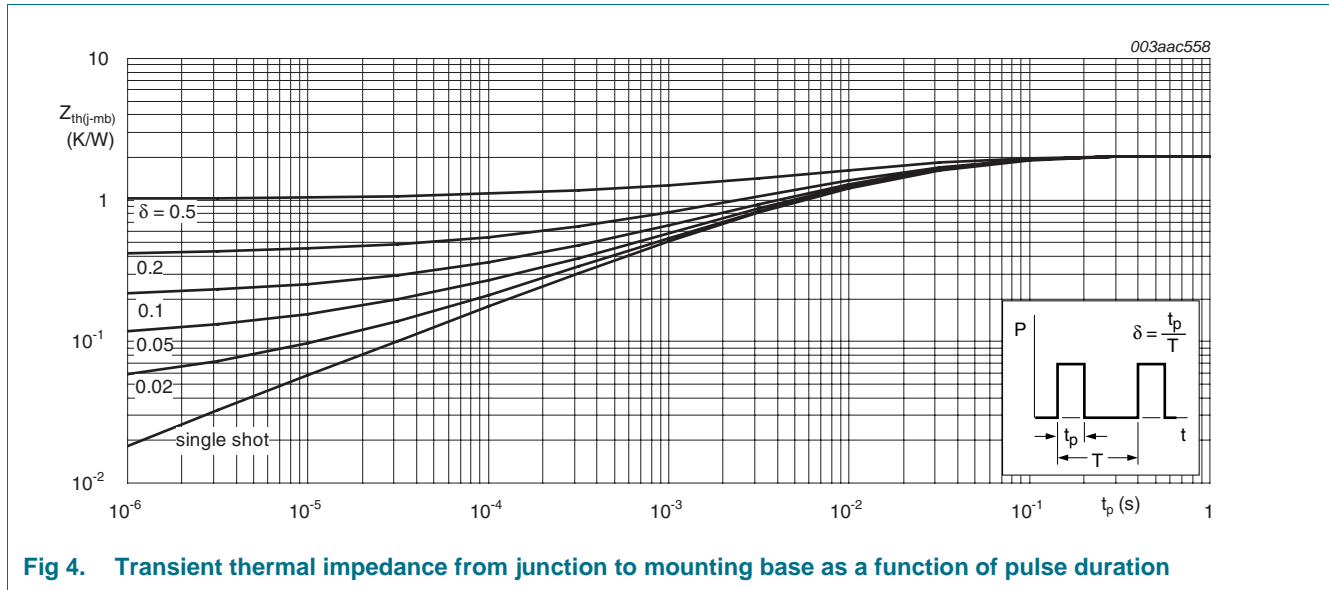


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

6. Characteristics

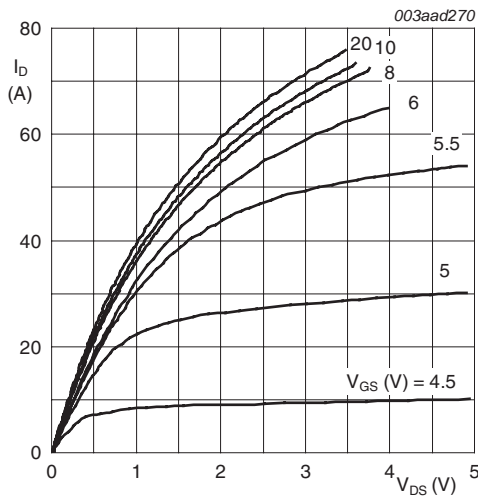
Table 6. Characteristics

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|--------------------------------|-----------------------------------|---|-----|------|------|---------------|
| Static characteristics | | | | | | |
| $V_{(BR)DSS}$ | drain-source breakdown voltage | $I_D = 250 \mu\text{A}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ }^\circ\text{C}$ | 73 | - | - | V |
| | | $I_D = 250 \mu\text{A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$ | 80 | - | - | V |
| $V_{GS(th)}$ | gate-source threshold voltage | $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ }^\circ\text{C};$ see Figure 10 ; see Figure 11 | 1 | - | - | V |
| | | $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ }^\circ\text{C};$ see Figure 10 ; see Figure 11 | - | - | 4.6 | V |
| | | $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ }^\circ\text{C};$ see Figure 10 ; see Figure 11 | 2 | 3 | 4 | V |
| I_{DSS} | drain leakage current | $V_{DS} = 80 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$ | - | - | 1.5 | μA |
| | | $V_{DS} = 80 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 125 \text{ }^\circ\text{C}$ | - | - | 10 | μA |
| I_{GSS} | gate leakage current | $V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$ | - | - | 100 | nA |
| | | $V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$ | - | - | 100 | nA |
| $R_{DS(on)}$ | drain-source on-state resistance | $V_{GS} = 10 \text{ V}; I_D = 5 \text{ A}; T_j = 175 \text{ }^\circ\text{C}$ | - | - | 66 | mΩ |
| | | $V_{GS} = 10 \text{ V}; I_D = 5 \text{ A}; T_j = 100 \text{ }^\circ\text{C};$ see Figure 12 | - | - | 42 | mΩ |
| | | $V_{GS} = 10 \text{ V}; I_D = 5 \text{ A}; T_j = 25 \text{ }^\circ\text{C};$ see Figure 13 | - | 20 | 27.5 | mΩ |
| R_G | internal gate resistance (AC) | $f = 1 \text{ MHz}$ | - | 0.8 | - | Ω |
| Dynamic characteristics | | | | | | |
| $Q_{G(tot)}$ | total gate charge | $I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$ | - | 17 | - | nC |
| | | $I_D = 25 \text{ A}; V_{DS} = 40 \text{ V}; V_{GS} = 10 \text{ V};$ see Figure 14 ; see Figure 15 | - | 20 | - | nC |
| Q_{GS} | gate-source charge | $I_D = 25 \text{ A}; V_{DS} = 40 \text{ V}; V_{GS} = 10 \text{ V};$ see Figure 15 | - | 6.4 | - | nC |
| $Q_{GS(th)}$ | pre-threshold gate-source charge | $I_D = 25 \text{ A}; V_{DS} = 40 \text{ V}; V_{GS} = 10 \text{ V};$ see Figure 14 | - | 3.7 | - | nC |
| $Q_{GS(th-pl)}$ | post-threshold gate-source charge | | - | 2.7 | - | nC |
| Q_{GD} | gate-drain charge | $I_D = 25 \text{ A}; V_{DS} = 40 \text{ V}; V_{GS} = 10 \text{ V};$ see Figure 14 ; see Figure 15 | - | 5 | - | nC |
| $V_{GS(pl)}$ | gate-source plateau voltage | $I_D = 25 \text{ A}; V_{DS} = 40 \text{ V}$ | - | 5 | - | V |
| C_{iss} | input capacitance | $V_{DS} = 40 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ }^\circ\text{C};$ see Figure 16 | - | 1200 | - | pF |
| C_{oss} | output capacitance | | - | 120 | - | pF |
| C_{rss} | reverse transfer capacitance | | - | 70 | - | pF |
| $t_{d(on)}$ | turn-on delay time | $V_{DS} = 40 \text{ V}; R_L = 1.6 \text{ }^\circ\Omega; V_{GS} = 10 \text{ V};$ $R_{G(ext)} = 4.7 \text{ }^\circ\Omega$ | - | 15 | - | ns |
| t_r | rise time | | - | 6 | - | ns |
| $t_{d(off)}$ | turn-off delay time | | - | 26 | - | ns |
| t_f | fall time | | - | 5 | - | ns |

Table 6. Characteristics ...continued

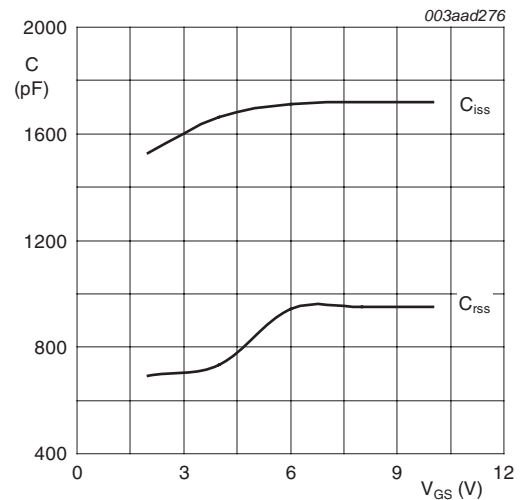
| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|---------------------------|-----------------------|--|-----|-----|-----|------|
| Source-drain diode | | | | | | |
| V_{SD} | source-drain voltage | $I_S = 5\text{ A}$; $V_{GS} = 0\text{ V}$; $T_j = 25\text{ °C}$; see Figure 17 | - | 0.8 | 1.2 | V |
| t_{rr} | reverse recovery time | $I_S = 15\text{ A}$; $di_S/dt = 100\text{ A}/\mu\text{s}$; $V_{GS} = 0\text{ V}$; | - | 36 | - | ns |
| Q_r | recovered charge | $V_{DS} = 40\text{ V}$ | - | 52 | - | nC |

[1] Tested to JEDEC standards where applicable.



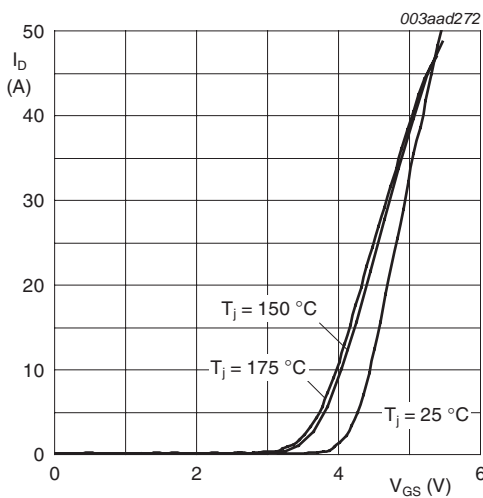
$T_j = 25\text{ °C}$; $t_p = 300\mu\text{s}$

Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values



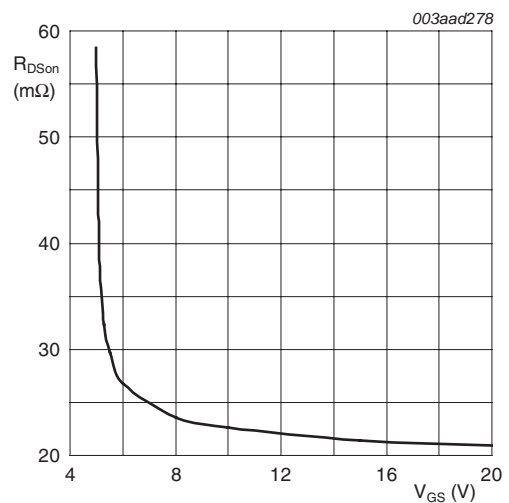
$V_{DS} = 0\text{ V}$; $f = 1\text{ MHz}$

Fig 6. Input and reverse transfer capacitances as a function of gate-source voltage; typical values



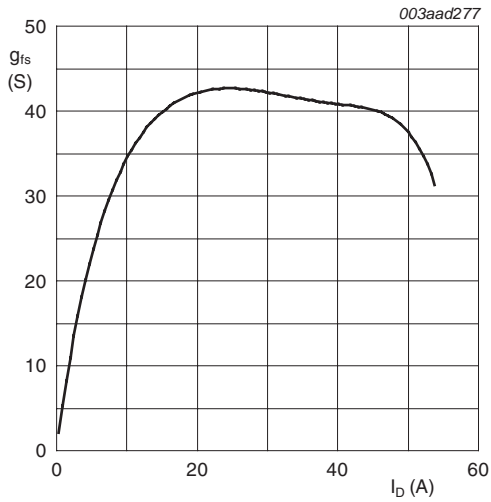
$V_{DS} = 15\text{ V}$

Fig 7. Transfer characteristics: drain current as a function of gate-source voltage; typical values



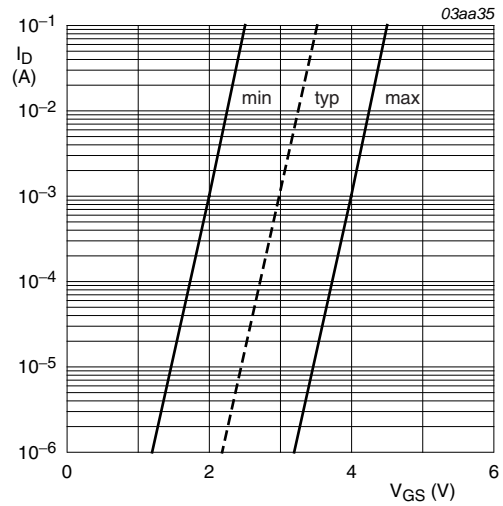
$T_j = 25\text{ °C}$; $I_D = 25\text{ A}$

Fig 8. Drain-source on-state resistance as a function of gate-source voltage; typical values



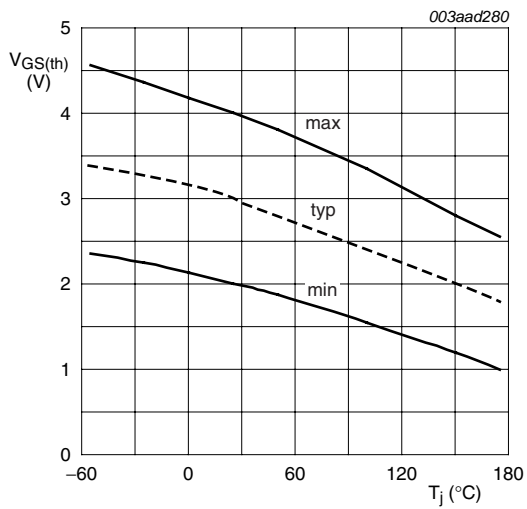
$T_j = 25\text{ }^\circ\text{C}; V_{DS} = 15\text{ V}$

Fig 9. Forward transconductance as a function of drain current; typical values



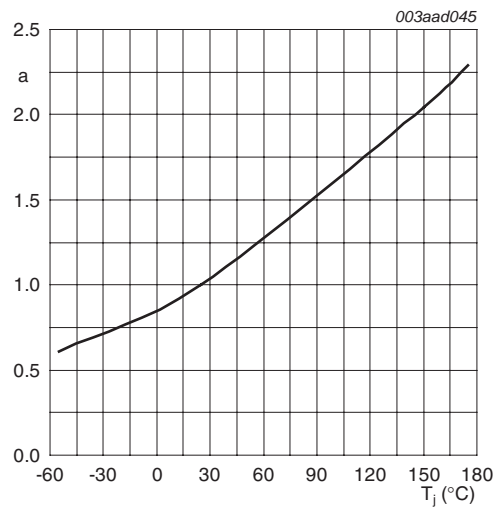
$T_j = 25\text{ }^\circ\text{C}; V_{DS} = 5\text{ V}$

Fig 10. Sub-threshold drain current as a function of gate-source voltage



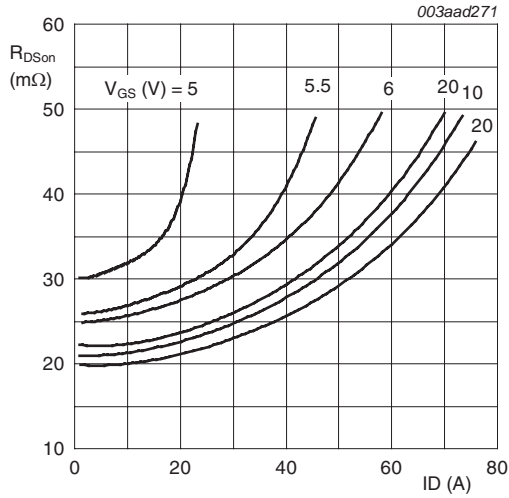
$I_D = 1\text{ mA}; V_{DS} = V_{GS}$

Fig 11. Gate-source threshold voltage as a function of junction temperature



$$a = \frac{R_{DSon}}{R_{DSon(25^\circ\text{C})}}$$

Fig 12. Normalized drain-source on-state resistance factor as a function of junction temperature



$T_j = 25^\circ\text{C}; t_p = 300\mu\text{s}$

Fig 13. Drain-source on-state resistance as a function of drain current; typical values

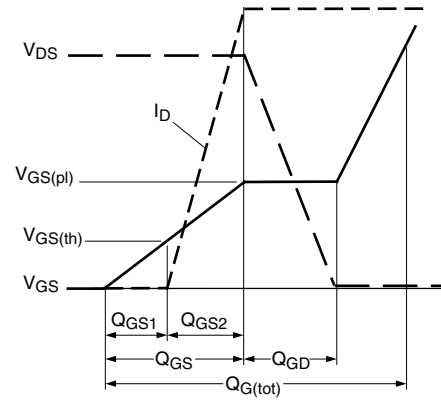
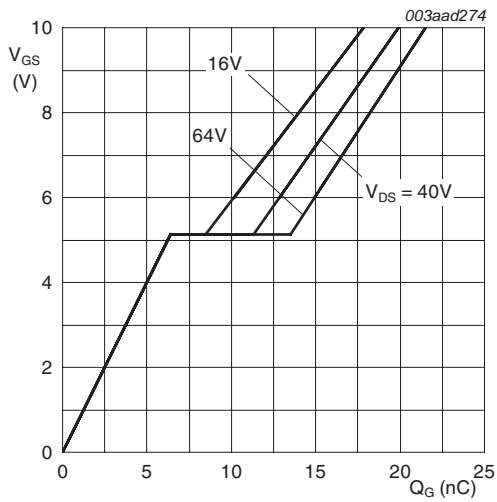
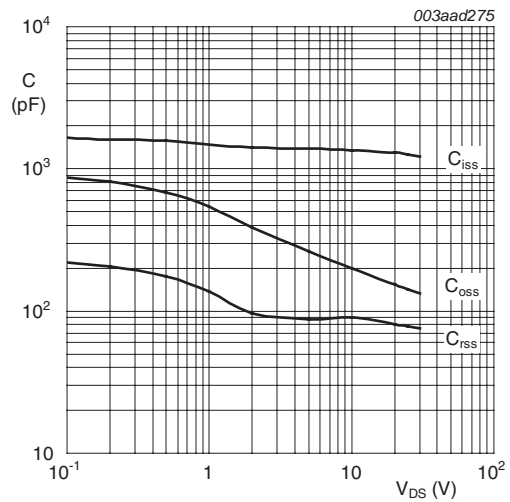


Fig 14. Gate charge waveform definitions



$T_j = 25^\circ\text{C}; I_D = 10\text{A}$

Fig 15. Gate-source voltage as a function of gate charge; typical values



$V_{GS} = 0\text{V}; f = 1\text{MHz}$

Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

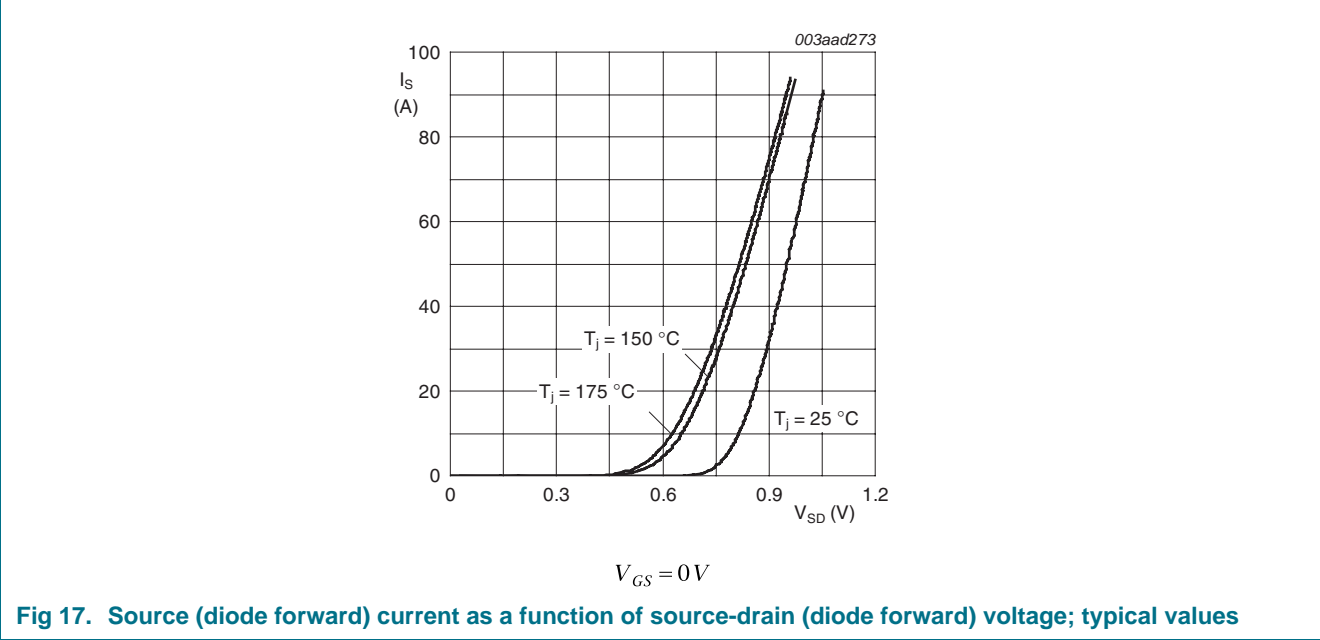


Fig 17. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

7. Package outline

Plastic single-ended surface-mounted package (LPAK); 4 leads

SOT669

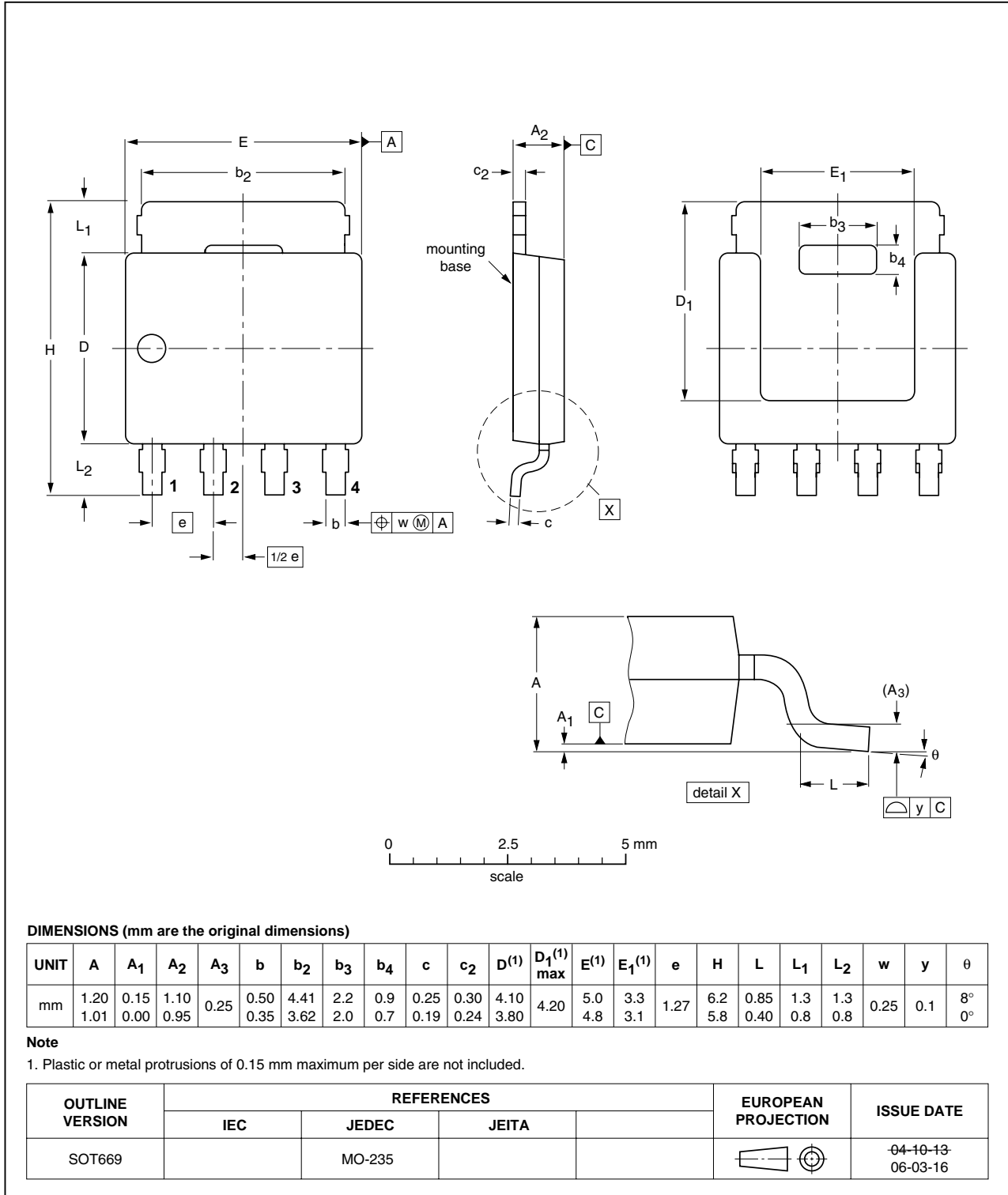


Fig 18. Package outline SOT669 (LPAK)

8. Revision history

Table 7. Revision history

| Document ID | Release date | Data sheet status | Change notice | Supersedes |
|----------------|--------------|--------------------|---------------|------------|
| PSMN026-80YS_1 | 20090625 | Product data sheet | - | - |

9. Legal information

9.1 Data sheet status

| Document status ^{[1][2]} | Product status ^[3] | Definition |
|-----------------------------------|-------------------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
| Product [short] data sheet | Production | This document contains the product specification. |

[1] Please consult the most recently issued document before initiating or completing a design.

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For more information, please visit: <http://www.nxp.com>

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